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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/042,811	01/08/2002	Charles A. Dark	072219-0278262 (P05109) 7599		
33402 ' 75	90 05/28/2003				
LAW OFFICES OF MARK C. PICKERING			EXAMINER		
P.O. BOX 300 PETALUMA, CA 94953			NGUYEN, JOSEPH H		
			ART UNIT	PAPER NUMBER	
			2815	in	
			DATE MAILED: 05/28/2003		

Please find below and/or attached an Office communication concerning this application or proceeding.

				AH
ر		Application No.	Applicant(s)	()
	Office Action Commence	10/042,811	DARK ET AL.	
	Office Action Summary	Examiner	Art Unit	
	The MAN INCOME.	Joseph Nguyen	2815	
Period fo	The MAILING DATE of this communication apor Reply	pears on the cover sheet with t	he correspondence address	
THE - Exte after - If the - If NO - Failt - Any	IORTENED STATUTORY PERIOD FOR REPL MAILING DATE OF THIS COMMUNICATION. Insions of time may be available under the provisions of 37 CFR 1. SIX (6) MONTHS from the mailing date of this communication. It is period for reply specified above is less than thirty (30) days, a reput of the provision of	136(a). In no event, however, may a reply ly within the statutory minimum of thirty (30 will apply and will expire SIX (6) MONTHS e, cause the application to become ABAND	be timely filed i) days will be considered timely, from the mailing date of this communication. IONED (35 U.S.C. § 133).	
1)	Responsive to communication(s) filed on	·		
2a)□	This action is FINAL . 2b)⊠ Th	nis action is non-final.		
3) Disposit	Since this application is in condition for allow closed in accordance with the practice under ion of Claims	ance except for formal matters Ex parte Quayle, 1935 C.D. 1	s, prosecution as to the merits is 1, 453 O.G. 213.	
4)🖂	Claim(s) 16-30 is/are pending in the application	on.		
	4a) Of the above claim(s) is/are withdra	wn from consideration.		
5)	Claim(s) is/are allowed.			
6)⊠	Claim(s) 16-30 is/are rejected.			
7)	Claim(s) is/are objected to.			
8)	Claim(s) are subject to restriction and/o	or election requirement.		
Applicati	ion Papers			
9)	The specification is objected to by the Examine	er.		
10)🛛	The drawing(s) filed on <u>08 January 2002</u> is/are:	: a)□ accepted or b)⊠ objected	to by the Examiner.	
	Applicant may not request that any objection to the		• •	
11) 🔲 1	The proposed drawing correction filed on	_ is: a)∭ approved b)∭ disar	pproved by the Examiner.	
	If approved, corrected drawings are required in re	· •		
	The oath or declaration is objected to by the Ex	aminer.		
Priority u	ınder 35 U.S.C. §§ 119 and 120			
13)	Acknowledgment is made of a claim for foreign	n priority under 35 U.S.C. § 11	9(a)-(d) or (f).	
a)[☐ All b)☐ Some * c)☐ None of:			
	1. Certified copies of the priority document	s have been received.		
	2. Certified copies of the priority document	s have been received in Applic	cation No	
* s	3. Copies of the certified copies of the prior application from the International Buse the attached detailed Office action for a list	reau (PCT Rule 17.2(a)).	-	
	cknowledgment is made of a claim for domesti	·		_
a) The translation of the foreign language pro Acknowledgment is made of a claim for domesti	ovisional application has been	received.	
Attachment				
2) Notice 3) Inform	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449) Paper No(s) 2	5) Notice of Inform	nary (PTO-413) Paper No(s) nal Patent Application (PTO-152)	
U.S. Patent and Tr PTO-326 (Res		tion Summary	Part of Paper No. 10	

Art Unit: 2815

DETAILED ACTION

Election/Restrictions

Applicant's election without traverse of claims 16-20 in Paper No. 9 is acknowledged. Therefore, claims 16-20, new claims 21-30 are prosecuted whereas claims 1-15 have been cancelled.

Drawings

The drawings are objected to under 37 CFR 1.83(a). The drawings must show every feature of the invention specified in the claims. Therefore, the limitation of "a first layer of dielectric material formed on the first section, the second section and the third doped region" in claim 16 must be shown or the feature(s) canceled from the claim(s). No new matter should be entered.

A proposed drawing correction or corrected drawings are required in reply to the Office action to avoid abandonment of the application. The objection to the drawings will not be held in abeyance.

Claim Rejections - 35 USC § 112

The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

Claims 16-20 are rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the enablement requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to enable one skilled in the art to

Art Unit: 2815

which it pertains, or with which it is most nearly connected, to make and/or use the invention. The limitation of "a first layer of dielectric material formed on the first section, the second section and the third doped region" in claim 16 is not disclosed in a way one of ordinary skill in the art can make and use.

Claims 17-20 are also rejected due to their dependency upon the rejected base claim 16 above.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 16, 21-30 are rejected under 35 U.S.C. 102(b) as being anticipated by Vinal.

Regarding claim 16, Vinal discloses on figure 1 an anti-fuse formed on a first semiconductor material 21 of a first conductivity type, the anti-fuse comprising a well 22 formed in the first semiconductor material, the well having a surface, a second conductivity type, and a dopant concentration; a first doped region 23 of the second conductivity type formed in the well, the first doped region having a dopant concentration that is greater than the dopant concentration of the well; a second doped region 33a of the first conductivity type formed in the well, the second doped region being spaced apart from the first doped region; a third doped region 24 formed in the

Application/Control Number: 10/042,811

Art Unit: 2815

well, the third doped region being spaced apart from the first and second doped regions; a layer of insulation material 41, 42 formed on the surface of the well, the layer of insulation material having a first opening (see element 31) that exposes the first doped region of the well, a second opening (see element 34) that exposes the second doped region of the well, and a third opening (see element 32) that exposes the third doped region of the well; a first section of a second semiconductor material 31 formed on the layer of insulation and the first region; a second section of the second semiconductor material 34 formed on the layer of insulation material and the second region, the second section being spaced apart from the first section; and a first layer of dielectric material formed on the first section, the second section and the third doped region.

Page 4

Regarding claim 21, Vinal discloses on figure 1 an anti-fuse formed on a semiconductor material 21 of a first conductivity type, the anti-fuse comprising a well 22 formed in the semiconductor material, the well having a surface, a second conductivity type, and a dopant concentration; a first doped region 23 of the second conductivity type formed in the well, the first doped region having a dopant concentration that is greater than the dopant concentration of the well; and a second doped region 33a of the first conductivity type formed in the well, the second doped region being spaced apart from the first doped region.

Regarding claim 22, Vinal discloses on figure 1a third doped region 24 formed in the well between the first and second doped regions 23, 33a; a metallic layer 34 formed on the third doped region; and a layer of insulation material 42 formed on the metallic

Art Unit: 2815

layer, the layer of insulation material being free of a conductive material that extends through the layer of insulation material and contacts the metallic layer.

Regarding claims 23-30, Vinal discloses on figure 1 all the structures set forth in the claimed invention.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 17-20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Vinal as applied to claim16 above, and further in view of Etou et al.

Regarding claim 17, Vinal discloses on figure 1 substantially all the structures set forth in the claimed invention except a first layer of silicide formed on the first polysilicon region. However, Etou et al discloses on figure 2B a first layer of silicide 31 formed on the first polysilicon region 34. In view of such teaching, it would have been obvious to one of ordinary skill in the art at the time the invention was made to modify Vinal by having a first layer of silicide formed on the first polysilicon region for the purpose of improving the current flow within a semiconductor device.

Regarding claims 18-20, Vinal and Etou et al together disclose all the structures set forth in the claimed invention.

Application/Control Number: 10/042,811

Art Unit: 2815

The prior art made of record and not relied upon is considered pertinent to

applicant's disclosure.

US Patent 6404026 B1 to Tsuyuki discloses a semiconductor device.

Conclusion

Page 6

Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Joseph Nguyen whose telephone number is (703) 308-

1269. The examiner can normally be reached on Monday-Friday, 7:30 am- 4:30 pm

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Eddie Lee can be reached on (703) 308-1690. The fax phone numbers for

the organization where this application or proceeding is assigned is (703) 308-7382 for

regular communications.

Any inquiry of a general nature or relating to the status of this application or

proceeding should be directed to the receptionist whose telephone number is (703) 308-

0956.

JN

May 15, 2003

EDDIE LEE

SUPERVISORY PATENT EXAMINER

TECHNOLOGY CENTER 2800